

UNISONIC TECHNOLOGIES CO., LTD

MMBT1015B

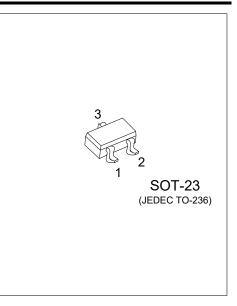
Preliminary

PNP SILICON TRANSISTOR

LOW FREQUENCY PNP AMPLIFIER TRANSISTOR

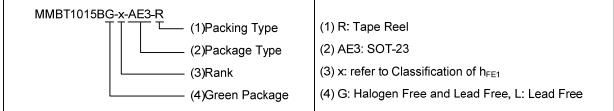
FEATURES

- * Collector-Emitter Voltage: BV_{CEO}= -50V
- * Collector current up to 150mA
- * High hFE linearity
- * Complement to MMBT1815



ORDERING INFORMATION

| Ordering Number | | Deekere | Pin Assignment | | | De alvie e | |
|---|--------------|---------|----------------|---|---|------------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing | |
| MMBT1015BL-x-AE3-R MMBT1015BG-x-AE3-R | | SOT-23 | В | ш | С | Tape Reel | |
| Note: Pin assignment: B: Base E: Emitter C: Collector | | | | | | | |
| | | | | | | | |



MARKING

| PACKAGE | MARKING | | | | |
|---------|---------------------------------|---------------------------------|--|--|--|
| | Y GR | | BL | | |
| SOT-23 | B4Y□ B4Y□ G: Halogen Free | B4G□ B4G□ G: Halogen Free | B4B□ L: Lead Free → G: Halogen Free | | |

■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------------|------------------|------------|------|
| Collector-Base Voltage | Vсво | -50 | V |
| Collector-Emitter Voltage | Vceo | -50 | V |
| Emitter-Base Voltage | VEBO | -5 | V |
| Collector Dissipation | Pc | 250 | mW |
| Collector Current | lc | -150 | mA |
| Base Current | lв | -50 | mA |
| Junction Temperature | TJ | +150 | °C |
| Storage Temperature | T _{STG} | -55 ~ +150 | °C |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------------|------------------|---|-----|-----|------|------|
| Collector-Base Breakdown Voltage | ВVсво | I _C = -100μA, I _E = 0 | -50 | | | V |
| Collector-Emitter Breakdown Voltage | BVCEO | I _C = -10mA, I _B = 0 | -50 | | | V |
| Emitter-Base Breakdown Voltage | BVEBO | I _E = -10μA, I _C = 0 | -5 | | | V |
| Collector-Emitter Saturation Voltage | VCE(SAT) | I _C = -100mA, I _B = -10mA | | | -0.3 | V |
| Base-Emitter Saturation Voltage | VBE(SAT) | I _C = -100mA, I _B = -10mA | | | -1.1 | V |
| Collector Cut-off Current | Ісво | $V_{CB} = -50V, I_E = 0$ | | | -100 | nA |
| Emitter Cut-off Current | I _{EBO} | V _{EB} = -5V, I _C = 0 | | | -100 | nA |
| | h _{FE1} | V _{CE} = -6V, I _C = -2mA | 120 | | 700 | |
| DC Current Gain | h _{FE2} | V _{CE} = -6V, I _C = -150mA | 25 | | | |
| Transition Frequency | f⊤ | V _{CE} = -10V, I _C = -1mA | 80 | | | MHz |

CLASSIFICATION OF h_{FE1}

| RANK | Y | GR | BL |
|-------|---------|---------|---------|
| RANGE | 120-240 | 200-400 | 350-700 |



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